

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
60V	35mΩ@10V	10A
	40mΩ@4.5V	

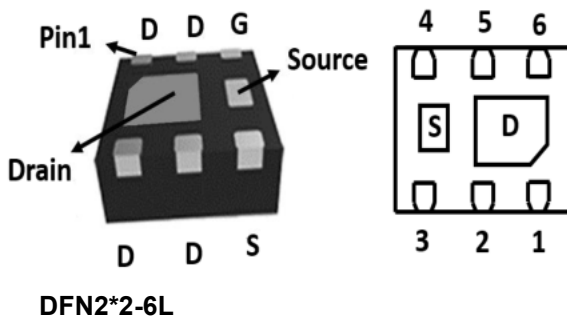
Feature

- Advanced trench process technology
- High density cell design for ultra low on-resistance
- High Speed switching

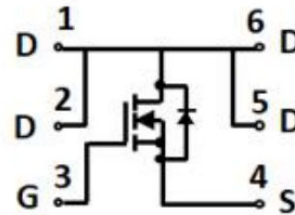
Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

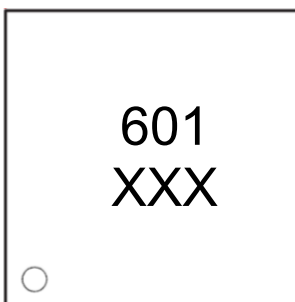
Package



Circuit diagram



Marking



Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	10	A
Pulsed Drain Current	I _{DM}	40	A
Power Dissipation	P _D	3	W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	42	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.2	1.6	2.5	V
Drain-source on-resistance ¹⁾	R _{DS(on)}	V _{GS} = 10V, I _D = 5A		25	35	mΩ
		V _{GS} = 4.5V, I _D = 5A		31	40	
Dynamic characteristics²⁾						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		570		pF
Output Capacitance	C _{oss}			70		
Reverse Transfer Capacitance	C _{rss}			64		
Total Gate Charge	Q _g	V _{DS} = 30V, V _{GS} = 10V, I _D = 5A		25		nC
Gate-Source Charge	Q _{gs}			5		
Gate-Drain Charge	Q _{gd}			6		
Turn-on delay time	t _{d(on)}	V _{DD} = 30V, V _{GS} = 10V, I _D = 5A, R _{GEN} = 3Ω		6		nS
Turn-on rise time	t _r			6		
Turn-off delay time	t _{d(off)}			17		
Turn-off fall time	t _f			3		
Source-Drain Diode characteristics						
Diode Forward Current ¹⁾	I _S				10	A
Diode Forward voltage	V _{DS}	V _{GS} = 0V, I _S = 10A			1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 10A di/dt = 100A/μs		30		nS
Reverse Recovery Charge	Q _{rr}			50		nC

Notes:

- 1) Pulse Test: Pulse Width < 300μs, Duty Cycle ≤2%.
- 2) Guaranteed by design, not subject to production testing.

Typical Characteristics

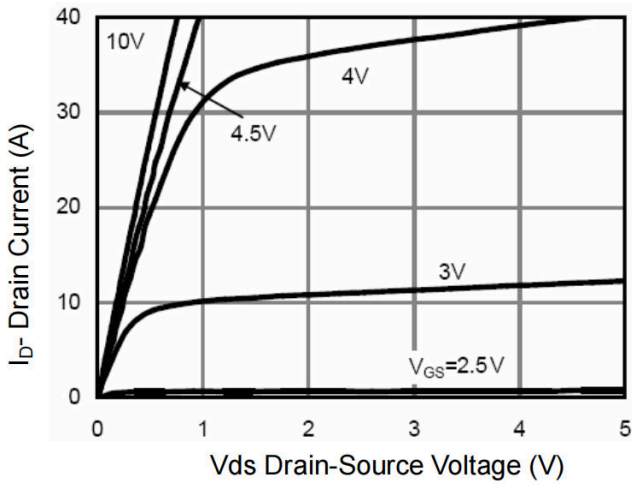


Figure 1 Output Characteristics

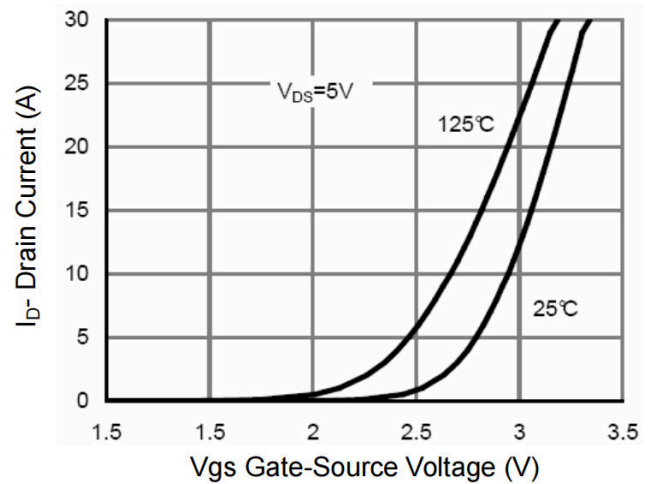


Figure 2 Transfer Characteristics

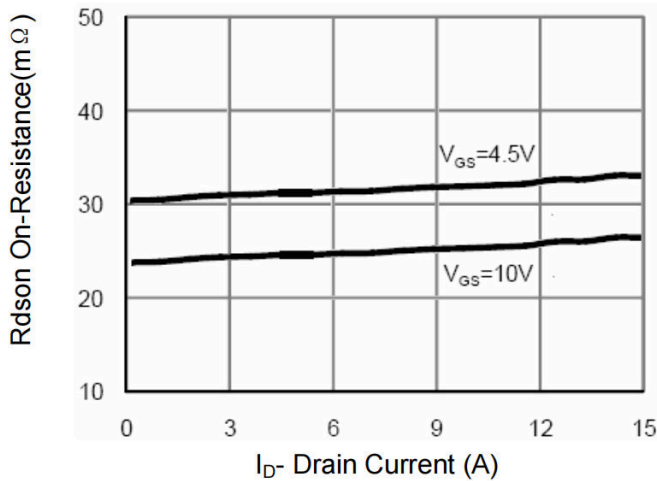


Figure 3 Rdson- Drain Current

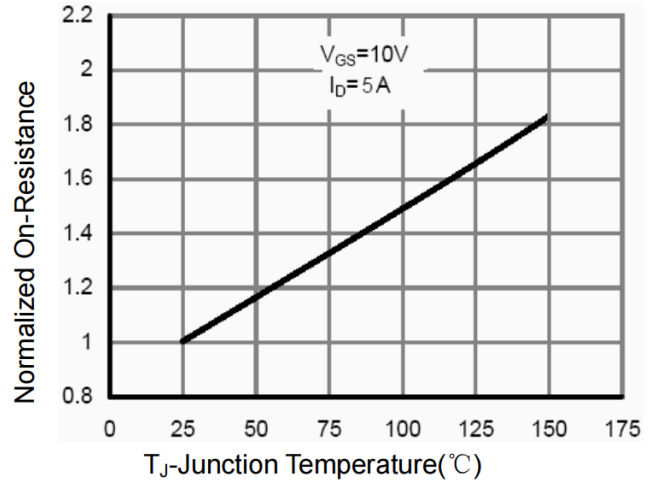


Figure 4 Rdson-Junction Temperature

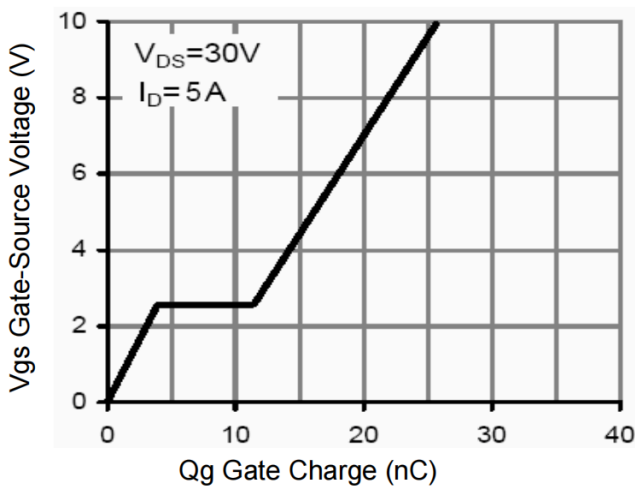


Figure 5 Gate Charge

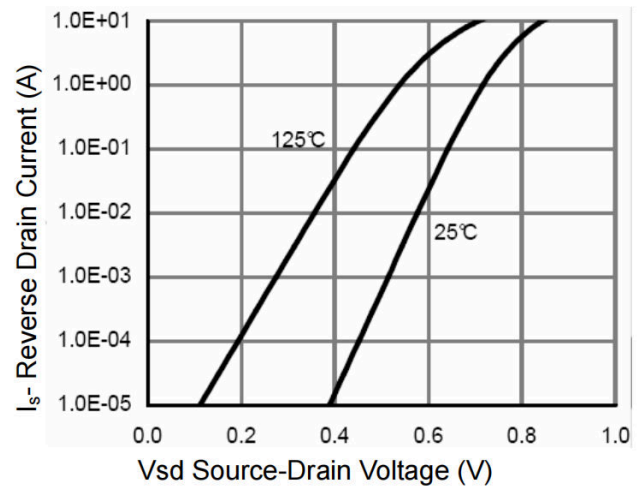


Figure 6 Source- Drain Diode Forward

Typical Characteristics

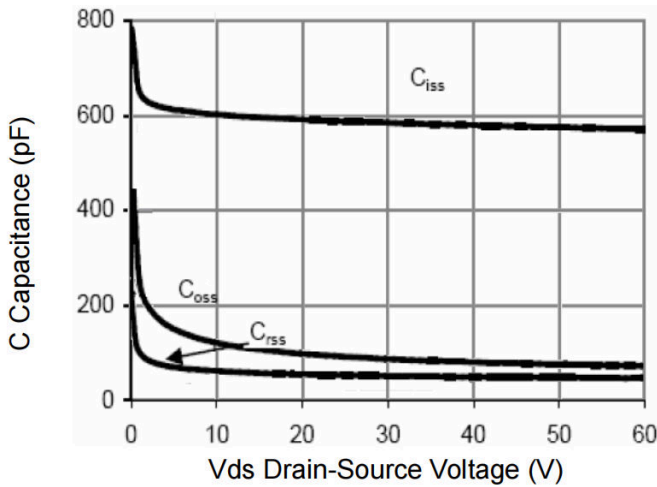


Figure 7 Capacitance vs Vds

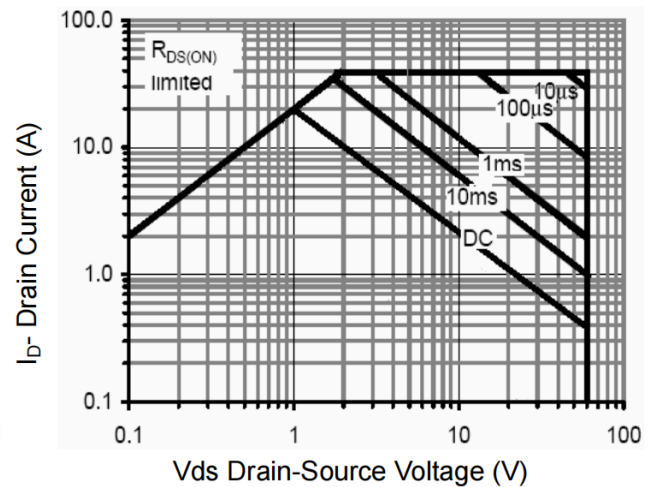


Figure 8 Safe Operation Area

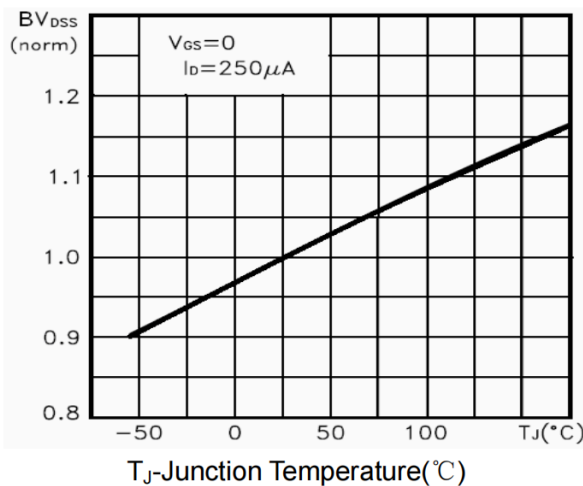


Figure 9 BV_{DSS} vs Junction Temperature

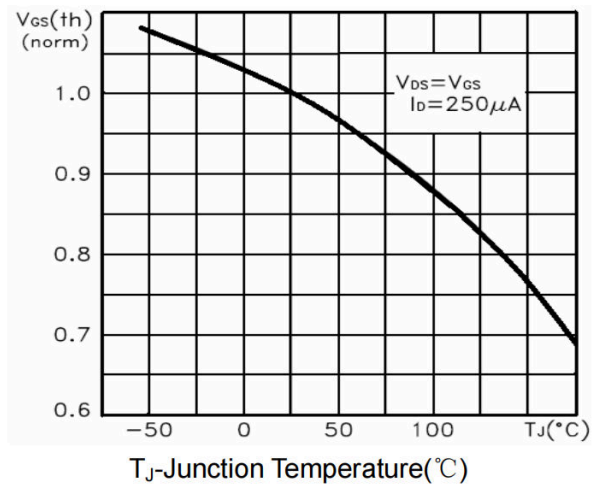


Figure 10 V_{GS(th)} vs Junction Temperature

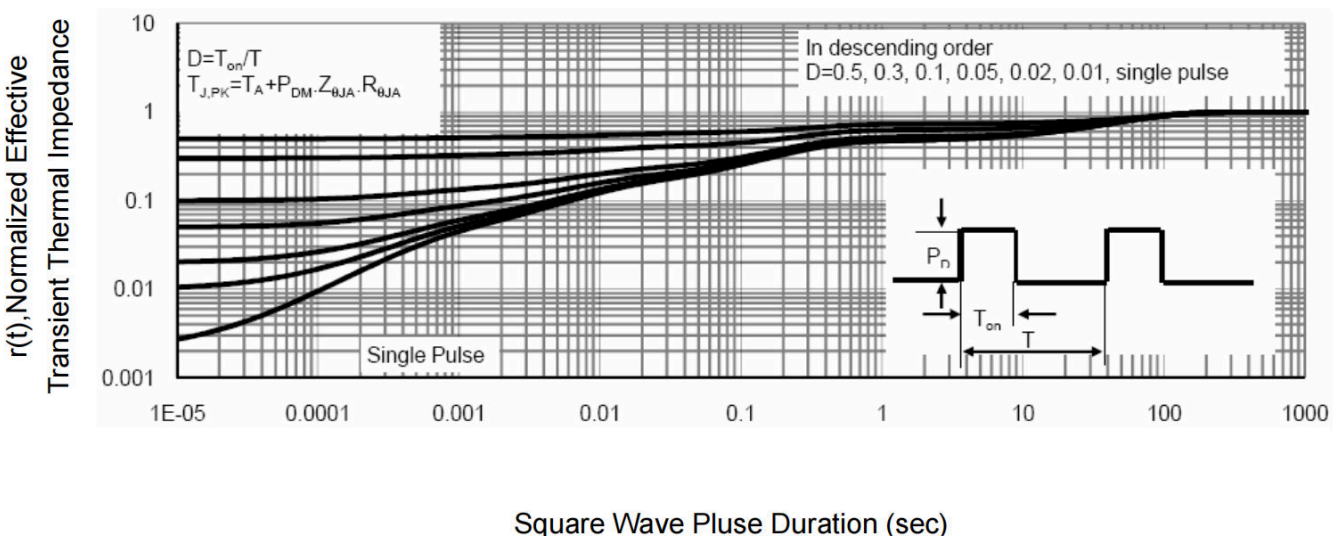
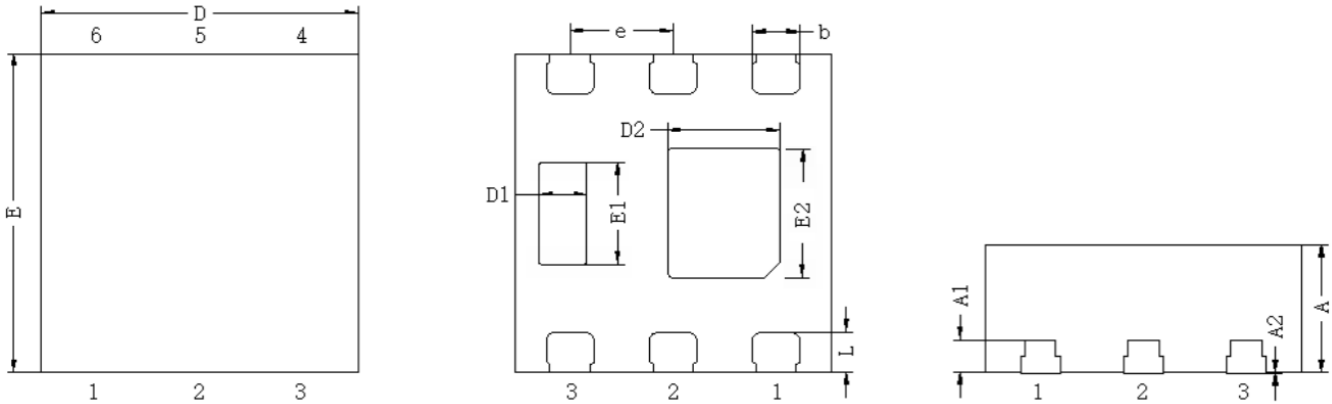


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN2*2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.850	0.028	0.033
A1	0.200 REF		0.008 REF	
A2	0.000	0.050	0.000	0.002
L	0.170	0.330	0.006	0.013
b	0.250	0.350	0.010	0.014
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
e	0.650 BSC		0.260 BSC	
D1	0.200	0.400	0.008	0.016
E1	0.460	0.660	0.018	0.026
D2	0.800	1.000	0.031	0.039
E2	0.850	1.050	0.033	0.041